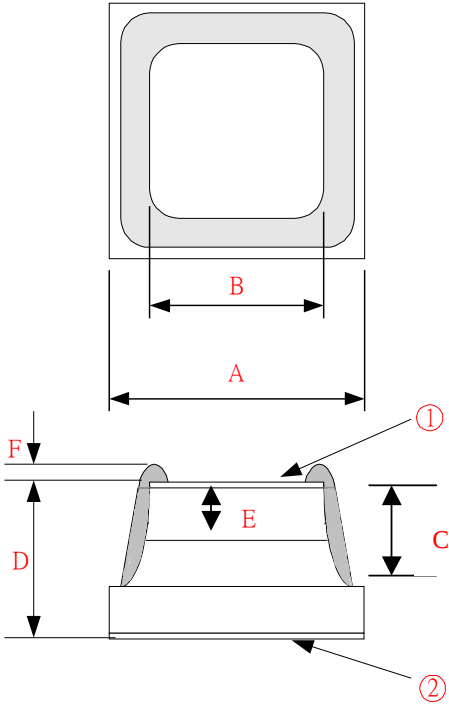


Product	Type													
Fast Rectifier Diodes	8GFNSC148-0800													
Metallization Top Al(4um) ① Bottom Al/Ti/Ni/Ag(2.6/0.3/0.3/1.0um) ②														
Dimension in millimeters <table border="1"> <thead> <tr> <th></th><th>Dimension</th></tr> </thead> <tbody> <tr> <td>A</td><td>1.48-0+0.03</td></tr> <tr> <td>B</td><td>1.06±0.05</td></tr> <tr> <td>C</td><td>0.12±0.03</td></tr> <tr> <td>D</td><td>0.25±0.02</td></tr> <tr> <td>E</td><td>0.04±0.01</td></tr> <tr> <td>F</td><td>0.03±0.02</td></tr> </tbody> </table>			Dimension	A	1.48-0+0.03	B	1.06±0.05	C	0.12±0.03	D	0.25±0.02	E	0.04±0.01	F
	Dimension													
A	1.48-0+0.03													
B	1.06±0.05													
C	0.12±0.03													
D	0.25±0.02													
E	0.04±0.01													
F	0.03±0.02													

Absolute Maximum Ratings (Ta=25℃)			
PEAK REVERSE VOLTAGE	VRM .. 800 V	JUNCTION TEMPERATURE	Tj ..125℃
PEAK FORWARD SURGE CURRENT	IFSM50 A	STORAGE TEMPERATURE RANGE	Tstg .. -65~150℃

Electrical Characteristics (sampling 100pcs per 1 lot)

Item	Symbol	Test Condition	Standard
FORWARD VOLTAGE	VF	IF=1.5A	1.3 V (MAX)
REVERSE CURRENT	IR	VR=800V	2μA (MAX)
BREAKDOWN VOLTAGE	BVR	IR=5μA	840V
REVERSE RECOVERY TIME	TRR	RG1	500nsec

Quality Assurance (sampling 50pcs per 1 lot)

Wafer Yield : >80%

HO CHIEN	Spec No.GPWF14808013RD	DATE: Jan .20.2005
----------	------------------------	--------------------